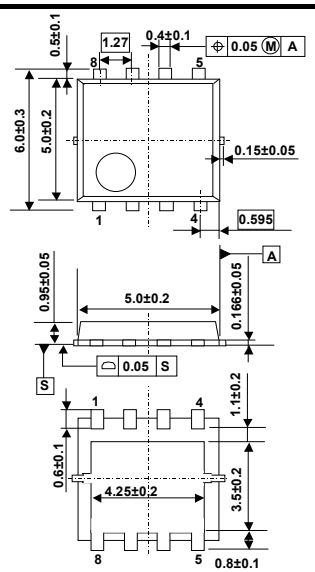
TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSⅣ)

TPCA8103

Lithium Ion Battery Applications
Notebook PC Applications
Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 3.1 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ =45S (typ.)
- Low leakage current: I_{DSS} = −10 μA (max) (V_{DS} = −30 V)
- Enhancement mode: V_{th} = −0.8 to −2.0 V (V_{DS} = −10 V, I_D = −1 mA)

Unit: mm



1,2,3 : SOURCE
4 : GATE
5,6,7,8 : DRAIN

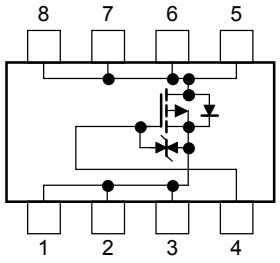
JEDEC	—
JEITA	—
TOSHIBA	2-5Q1A

Weight: 0.076 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	− 40	A
	Pulsed (Note 1)	I_{DP}	−120	
Drain power dissipation (Tc=25°C)		P_D	45	W
Drain power dissipation (t = 10 s) (Note 2a)		P_D	2.8	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.6	W
Single pulse avalanche energy (Note 3)		E_{AS}	208	mJ
Avalanche current		I_{AR}	− 40	A
Repetitive avalanche energy (Tc=25°C) (Note 4)		E_{AR}	4.5	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Circuit Configuration



Note: For (Note 1), (Note 2), (Note 3), (Note 4), please refer to the next page.

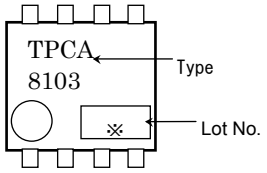
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic sensitive device. Please handle with caution.

Thermal Characteristics

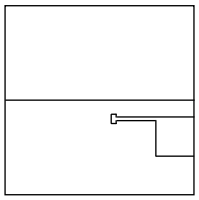
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	$R_{th\ (ch\text{-}c)}$	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	78.1	°C/W

Marking (Note 5)



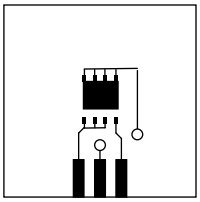
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

(a)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

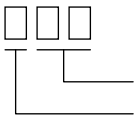
(b)

Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 100μH, R_G = 25 Ω, I_{AR} = − 40 A

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: O on lower left of the marking indicates Pin 1.

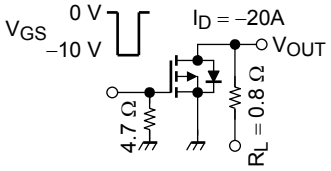
※ Weekly code: (Three digits)



Week of manufacture
(01 for first week of year, continues up to 52 or 53)

Year of manufacture
(One low-order digits of calendar year)

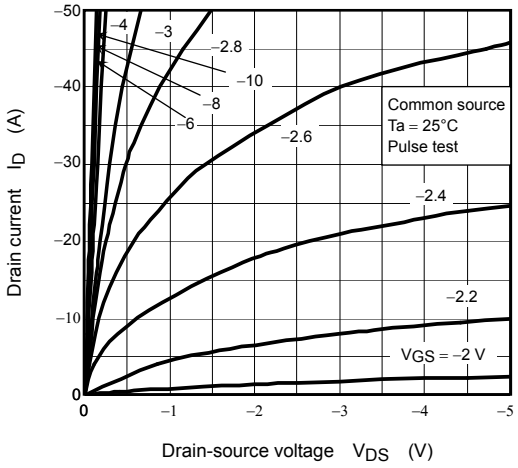
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-OFF current		I_{DSS}	V_{DS} = −30 V, V_{GS} = 0 V	—	—	−10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−30	—	—	V
		$V_{(BR)\ DSX}$	I_D = −10 mA, V_{GS} = 20 V	−13	—	—	
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = − 1 mA	−0.8	—	−2.0	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = −4 V, I_D = −20 A	—	5.2	6.8	mΩ
			V_{GS} = −10 V, I_D = −20 A	—	3.1	4.2	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −20 A	22.5	45	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	7880	—	pF
Reverse transfer capacitance		C_{rss}		—	1340	—	
Output capacitance		C_{oss}		—	1450	—	
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	15	—	ns
	Turn-ON time	t_{on}		—	13	—	
	Fall time	t_f		—	251	—	
	Turn-OFF time	t_{off}		—	596	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ −24 V, V_{GS} = −10 V, I_D = −40 A	—	184	—	nC
Gate-source charge 1		Q_{gs1}		—	12	—	
Gate-drain (“miller”) charge		Q_{gd}		—	58	—	

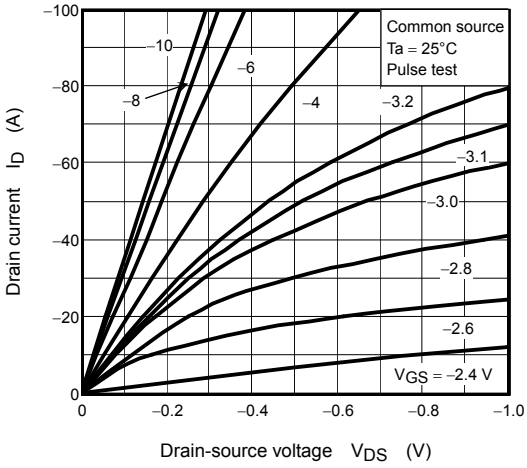
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	−120	A
Forward voltage (diode)		V_{DSF}	I_{DR} = −40 A, V_{GS} = 0 V	—	—	1.2	V

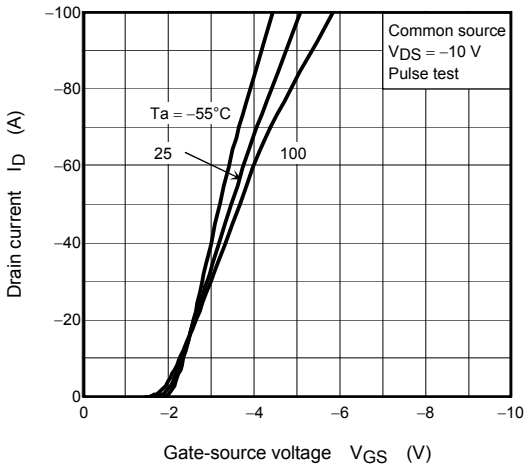
$I_D - V_{DS}$



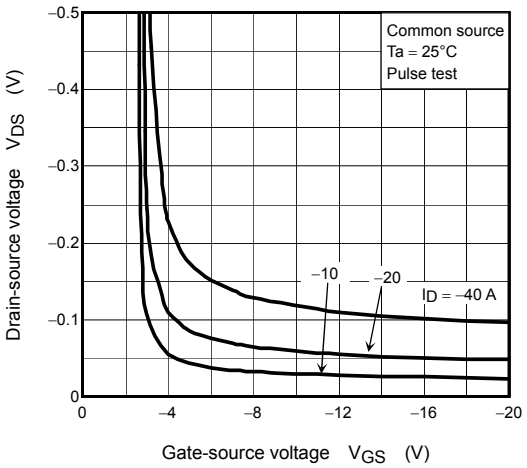
$I_D - V_{DS}$



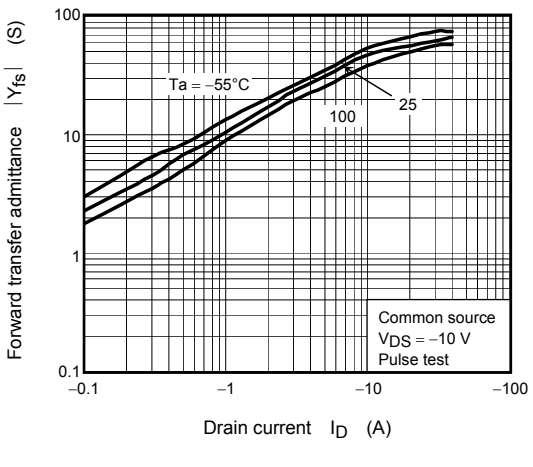
$I_D - V_{GS}$



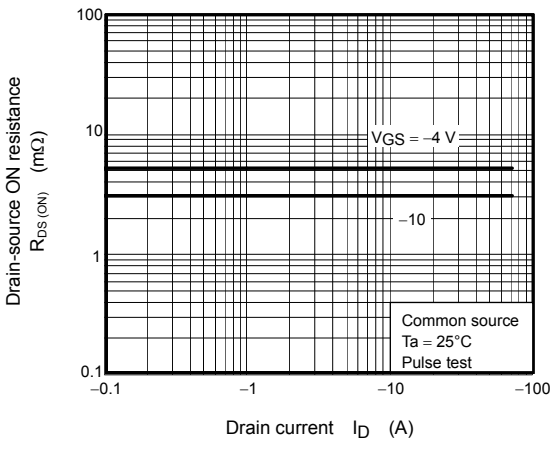
$V_{DS} - V_{GS}$



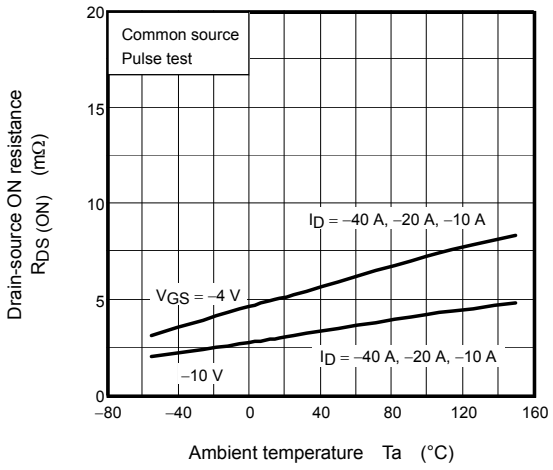
$|Y_{fs}| - I_D$



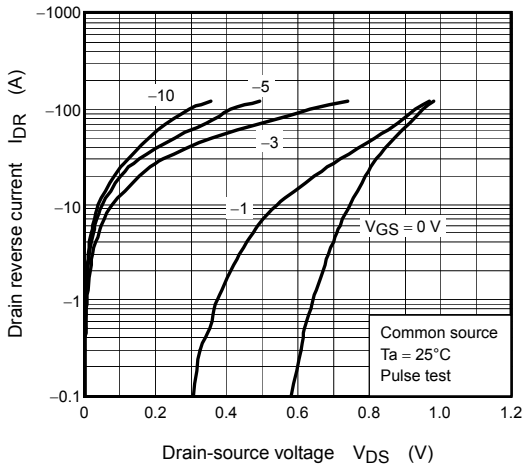
$R_{DS\ (ON)} - I_D$



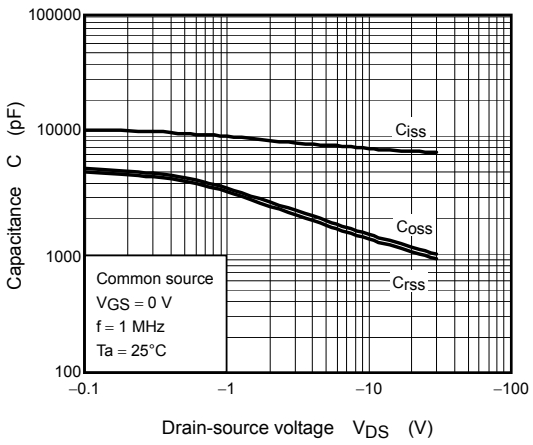
$R_{DS\ (ON)}$ – Ta



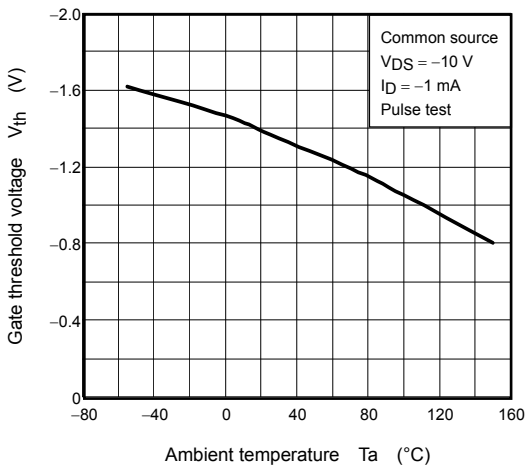
I_{DR} – V_{DS}



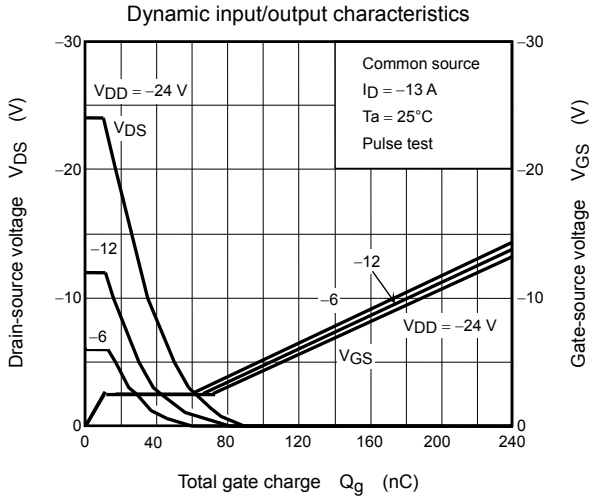
Capacitance – V_{DS}



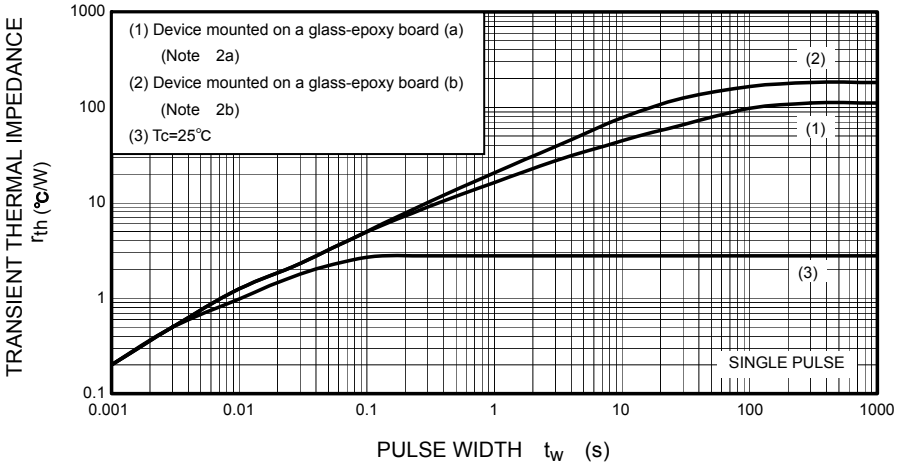
V_{th} – Ta



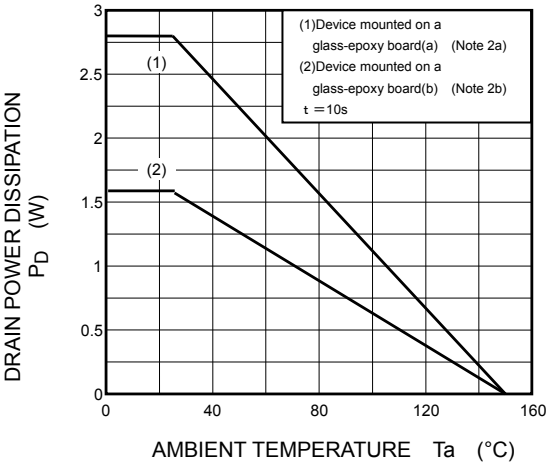
Dynamic input/output characteristics



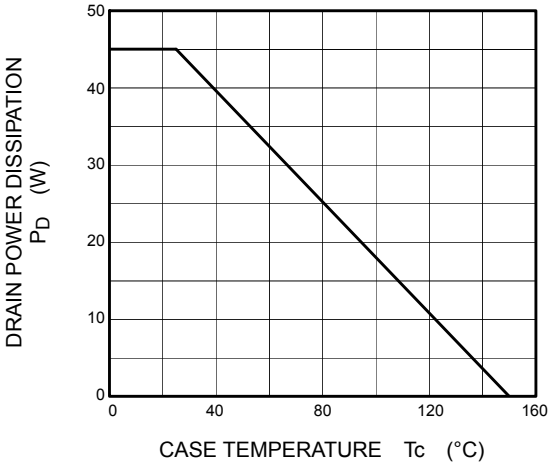
$r_{th} - t_w$



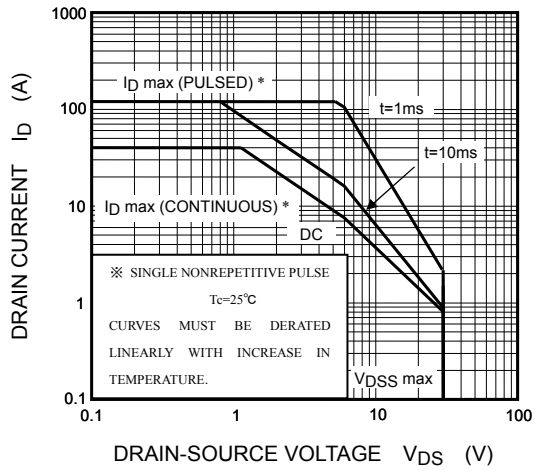
$P_D - Ta$



$P_D - Tc$



SAFE OPERATING AREA



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